

IN THE SPECIFICATION:

Please amend paragraph [0021] as follows:

[0021] In another specific embodiment, a glass substrate with 7000 angstrom amorphous-silicon emitters formed thereon was dipped in a solution of propan-1-ol, as the solvent, and NaCl for 15 minutes at a temperature just below boiling. The result was an approximately 7000 angstrom alpha-silicon/glass structure with Na doped therein. SIMS analysis of H, P, and Na were conducted comparing a similar sample that had not been dipped. The NaCl dipped structure had about 500 times higher Na near the Si surface (at about 500 angstroms depth) than the sample that had not been dipped. The Na level remained higher throughout the 7000 angstroms tested, but decreased to about 80 times higher near the Si/glass interface (at about 6000 angstroms). Further, the dipped sample included a slightly higher P than the undipped sample, but the difference was less than about 1.5 times. No H difference was seen between the samples. Mo contamination (due to use of a furnace having ~~MO~~ Mo therein) was detected on the NaCl dipped sample, but no Mo was seen in the undipped sample. Mo contamination is avoided in other embodiments. Higher K and Ca were also observed in the NaCl dipped sample. Surprisingly, Cl was not detected in either the dipped or undipped sample. This is an important finding as Cl has a high work function and is undesirable in the emitter tip.